

(Following Paper ID and Roll No. to be filled in your Answer Book)

PAPER ID : 3033

Roll No.

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B.Tech.

FIRST SEMESTER EXAMINATION, 2005-2006

ELECTRONICS ENGINEERING

Time : 3 Hours

Total Marks : 100

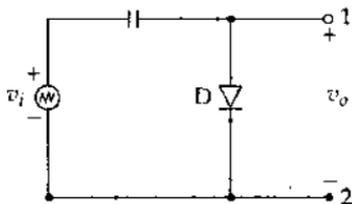
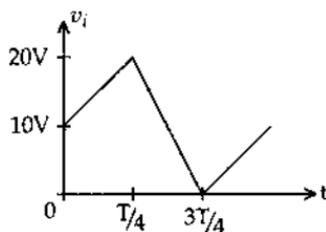
- Note :**
- Answer ALL questions.
 - All questions carry equal marks.
 - In case of numerical problems assume data wherever not provided.
 - Be precise in your answer.

1. Attempt *any four* of the following questions : (5x4=20)
- Distinguish between intrinsic and extrinsic semiconductor. What is the effect of temperature on conductivity of a semiconductor ?
 - How are the carrier mobilities related with resistivity of a semiconductor ? Does a 'hole' in a semiconductor contribute to a flow of current ? If yes, how and if no, how ?
 - Discuss the current flow mechanism in a p-n junction under -
 - no bias
 - forward bias
 - reverse bias conditions.

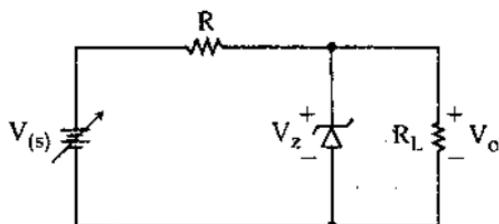
- (d) A germanium diode carries a current of 1mA at room temperature when a forward bias of 0.15V is applied. Estimate the reverse saturation current at room temperature.
- (e) Which is more sensitive to a change in temperature, forward current or reverse current? Explain why?
- (f) Explain, the transition capacitance and diffusion capacitance of a p-n junction.

2. Attempt *any two* of the following questions : (10x2=20)

- (a) What is transformer utilisation factor? Determine the rating of a transformer to deliver a 100 Watts of d.c. power to a load under full wave rectifier.
- (b) Distinguish between clipping and clamping circuits. Draw the waveform observed on an oscilloscope in dc mode when connected between 1 and 2 of the following circuit with shown v_i applied. Indicate voltages and the zero level. Also give the numerical values of the reading of a d.c. voltmeter connected across 1 and 2. Find the PIV of the diode.

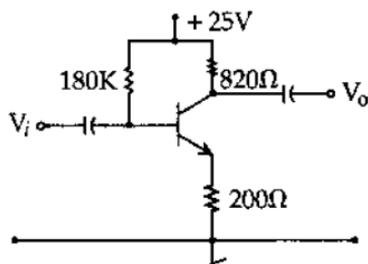


- (c) Explain 'Avalanche' break down. Draw the $v-i$ characteristics of zener diode and explain how does a zener regulate a voltage? The input voltage for the following figure varies from 35V to 45V, $V_Z = 20V$, $r_Z = 5\Omega$, $I_L(\text{min}) = 0\text{mA}$, $I_L(\text{max}) = 100\text{mA}$, $I_Z(\text{min}) = 10\text{mA}$, $I_Z(\text{max}) = 400\text{mA}$. Find the values of R and $P_Z(\text{max})$.



3. Attempt *any four* of the following questions : (5x4=20)

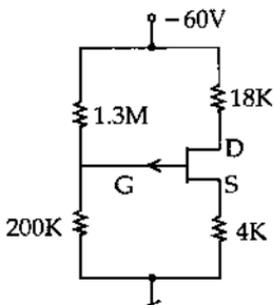
- (a) Define with respect to BJT the following.
- (i) I_{CO} (ii) α (iii) β
- (iv) I_{CEO} (v) I_{CBO}
- (b) Draw and explain the input and output characteristics of common base configuration of BJT. Indicate all the region of operations.
- (c) Find I_C and V_{CE} for the following circuit if $\beta = 80$ for the BJT.



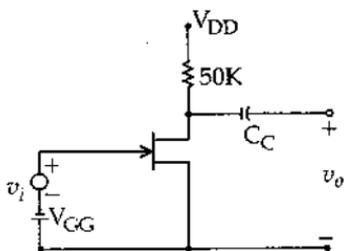
- (d) The collector and base current of n-pn transistor are measured as $I_c = 5 \text{ mA}$, $I_B = 50 \mu\text{A}$ and $I_{cBo} = 1 \mu\text{A}$.
- Determine α , β and I_E .
 - Determine the new level of I_B required to produce $I_c = 10 \text{ mA}$.
- (e) Explain how operating point is selected for amplification in CE mode using Graphical method only.
- (f) Derive the voltage gain, current gain expressions for a potential divider biased common emitter amplifier using h parameters.

4. Attempt *any two* of the following questions : (10x2=20)

- (a) Write notes on the following :
- depletion type MOSFET
 - Pinch-off voltage
 - Transfer characteristics of JFET
 - Transconductance
- (b) Consider the following circuit. Determine I_D , V_{GS} and V_{DS} for $|I_{DSS}| = 4 \text{ mA}$, $V_P = 4\text{V}$.

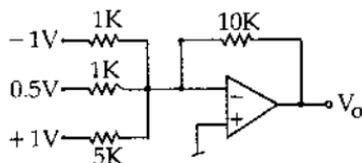


aktuonline.com Calculate the voltage gain and output resistance of the following circuit. Given that $g_m = 2\text{mA/V}$ and $r_d = 10\text{k}$.
 (c) aktuonline.com

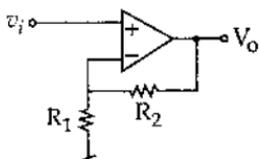
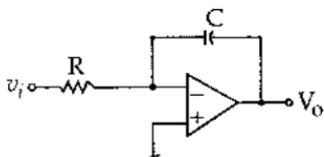


5. Attempt *any four* of the following questions : (5x4=20)

(a) Enlist the ideal characteristics of an op-amp. Why op-amp is called operational amplifier. Find out the voltage output of the following circuit.



(b) Determine the output of both of the circuits.



(c) Convert the following numbers as indicated :

(i) $(1001)_8 = (\quad)_2$

(ii) $(2CCD)_{16} = (\quad)_5$

(iii) $(0.45)_{10} = (\quad)_8$

(iv) $(345)_8 = (\quad)_{10}$

(v) $(7841)_9 = (\quad)_{10}$

(d) (i) Realise AND, OR, NOT using only NAND gates.

(ii) Using NOR gates only realise Ex - OR gate.

(e) Minimise using K-Map $f(A, B, C, D) = \Sigma(1, 3, 5, 7, 9, 11, 13, 15)$ then convert the minimised function into POS.

(f) Write notes on the following :

(i) Demorgan's Theorem

(ii) Canonical form of Boolean function

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